

TO-251/252 Plastic-Encapsulated Transistors

D882 TRANSISTOR (NPN)

FEATURES

Power dissipation

$$P_{CM}: 1.25 \text{ W (Tamb=25}^\circ\text{C)}$$

Collector current

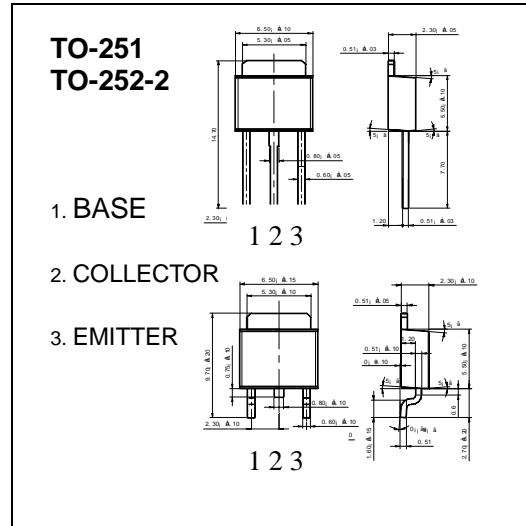
$$I_{CM}: 3 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: 40 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}, I_E = 0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10 \text{ mA}, I_B = 0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}, I_C = 0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB} = 40\text{V}, I_E = 0$			1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 30\text{V}, I_B = 0$			10	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 6\text{V}, I_C = 0$			1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 2\text{V}, I_C = 1\text{A}$	60		400	
	$h_{FE(2)}$	$V_{CE} = 2\text{V}, I_C = 100\text{mA}$	32			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 2\text{A}, I_B = 0.2\text{A}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 2\text{A}, I_B = 0.2\text{A}$			1.5	V
Transition frequency	f_T	$V_{CE} = 5\text{V}, I_C = 0.1\text{A}$ $f = 10\text{MHz}$	50			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400